

**EAST Search History****EAST Search History (Prior Art)**

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**EAST Search History (Interference)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"6,407,359".pn.	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:22
L2	9	"5026533".pn. or "4923687".pn. or "5654459".pn. or "6291698".pn. or "6222056".pn. or "6680038".pn. or "7204963".pn. or "6727375".pn. or "7507850".pn.	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:44
L3	6	12/375033 or 12/681114 or 12/744204 or 12/738799 or 12/999240	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:46
L5	4	10/586675	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:46
L6	1	"20090259063"	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:47
L7	3	"20100274028" or "20100296994" or "20100270296"	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:48
L8	53	("Sio.sub.2" or silicon \$2oxide) (network or structure or backbone) same low (k or dielectric)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/18 07:49
S221	58403	(propyhnethylmethoxysilane or methyl orthosilicate or n-propyl orthosilicate, tetrabutyl glycol orthosilicate, anayltrimethoxysilane, bis ((methyltriethyleneglycol)dinaethylsilane or 2-(cyclohex 3-enyl)ethyltriethoxysilane or cyclohexylmethyldimethoxysilane or cyclohexylmethyldimethoxysilane or cyclopentylmethyldimethoxysilane, cyclopentyltrimethoxysilane or di-i-butyldimethoxysilane or di-i-propyldimethoxysilane or dicyclopentylmethoxysilane or dimethyldethoxysilane or diphenyldimethoxysilane or vinyltriacetoxysilane or 2-phenylethyltriethoxysilane or 2-phenylethylmethyldiethoxysilane or 3-methacryloxypropyltrimethoxysilane or 3-acryloxypropyltrimethoxysilane or 3-methacryloxy-2-methyl-propyltrimethoxysilane or 3- acryloxy-2-methylpropylmethoxysilane, methyldiethoxysilane or methylpropylmethoxysilane or	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:04

		methylpropyldimethoxsilane or trimethoxsilane or triethoxsilane or dimethylmethoxsilane or triethylsilane or methyltriacetoxysilane or ethyltriacetoxysilane or vinyltriacetoxysilane or di-tert-butoxydiacetoxysilane or heptamethyldisilazane or hexamethyldisilazane or N,O-bis(trimethylsilyl)acetamide or 1,3-divinyltetramethyldisilazane or hexamethyldisiloxane or 1,3-divinyltetramethyldisiloxane or 1,1,3,3-tetramethyldisiloxane or 3-acetoxypropyltrimethoxysilane or 3-acetoxypropyltriethoxysilane or trimethylsilyl acetate or 3-azido-propyltriethoxysilane or N-(n-butyl)-3-aminopropyltrimethoxysilane or 3-amino-propyltrimethoxysilane or 3-aminopropyltriethoxysilane)				
S222	8182	S221 and (SiO <sub>2</sub> or silicon dioxide)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:07
S223	2460	S221 and (SiO <sub>2</sub> or silicon dioxide) and (CVD or chemical vapor deposition)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:08
S224	821	S223 and (propynethyldimethoxsilane or methyl orthosilicate or n-propyl orthosilicate, tetrabutyl glycol orthosilicate, analytrimethoxysilane, bis (methyltriethyleneglycol)dinaethylsilane or 2-(cyclohex 3-enyl)ethyltriethoxysilane or cyclohexylmethyldimethoxysilane or cyclohexylmethyltrimethoxysilane or cyclopentylmethyldimethoxysilane, cyclopentyltrimethoxysilane or di-i-butyldimethoxysilane or di-i-propyldimethoxysilane or dicyclopentyldimethoxysilane or dimethyldiethoxysilane or diphenyldimethoxysilane or vinyltriacetoxysilane or 2-phenylethyltriethoxysilane or 2-phenylethylmethyltriethoxysilane or 3-methacryloxypropyltrimethoxysilane or 3-acryloxypropyltrimethoxysilane or 3-methacryloxy-2-methyl-propyltrimethoxysilane or 3-acryloxy-2-methylpropyltrimethoxysilane, methyldiethoxysilane or methylpropyldiethoxysilane or methylpropyldimethoxysilane or trimethoxysilane or triethoxysilane or dimethylmethoxysilane or triethylsilane or methyltriacetoxysilane or ethyltriacetoxysilane or vinyltriacetoxysilane or di-tert-butoxydiacetoxysilane or heptamethyldisilazane or hexamethyldisilazane or N,O-bis(trimethylsilyl)acetamide or 1,3-divinyltetramethyldisilazane or hexamethyldisiloxane or 1,3-divinyltetramethyldisiloxane or 1,1,3,3-tetramethyldisiloxane or 3-acetoxypropyltrimethoxysilane or 3-acetoxypropyltriethoxysilane or trimethylsilyl acetate or 3-azido-propyltriethoxysilane or N-(n-butyl)-3-aminopropyltrimethoxysilane or 3-amino-propyltrimethoxysilane or 3-aminopropyltriethoxysilane) same (vapor deposition or CVD or precursor or SiO <sub>2</sub> or "sio.	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:09

		sub.2" or silicon dioxide)				
S225	18239	S221 and (SiO2 or "sio.sub.2" or silicon dioxide)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:09
S226	4365	S221 and (SiO2 or "sio.sub.2" or silicon dioxide) and (CVD or chemical vapor deposition)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:09
S227	1405	S226 and (propynethyldimethoxysilane or methyl orthosilicate or n-propyl orthosilicate, tetrabutyl glycol orthosilicate, ananyltrimethoxysilane, bis (methyltriethyleneglycol)dinaethylsilane or 2-(cyclohex 3-enyl)ethyltrimethoxysilane or cyclohexylmethyldimethoxysilane or cyclohexylmethyltrimethoxysilane or cyclopentylmethyldimethoxysilane, cyclopentyltrimethoxysilane or di-i-butylmethoxysilane or di-i-propylmethoxysilane or dicyclopentyldimethoxysilane or dimethyldethoxysilane or diphenyldimethoxysilane or vinyltriacetoxysilane or 2-phenylethyltrimethoxysilane or 2-phenylethylmethyldiethoxysilane or 3-methacryloxypropyltrimethoxysilane or 3-acryloxypropyltrimethoxysilane or 3-methacryloxy-2-methyl-propyltrimethoxysilane or 3-acryloxy-2-methylpropylmethoxysilane, methyldiethoxysilane or methylpropylmethoxysilane or methylpropyltrimethoxysilane or trimethoxysilane or triethoxysilane or dimethylethoxysilane or triethylsilane or methyltriacetoxysilane or ethyltriacetoxysilane or vinyltriacetoxysilane or di-tert-butoxydiacetoxysilane or heptamethyldisilazane or hexamethyldisilazane or N,O-bis(trimethylsilyl)acetamide or 1,3-divinyltetramethyldisilazane or hexamethyldisiloxane or 1,3-divinyltetramethyldisiloxane or 1,1,3,3-tetramethyldisiloxane or 3-acetoxypropyltrimethoxysilane or 3-acetoxypropyltriethoxysilane or trimethylsilyl acetate or 3-azido-propyltriethoxysilane or N-(n-butyl)-3-aminopropyltrimethoxysilane or 3-amino-propyltrimethoxysilane or 3-aminopropyltriethoxysilane) same (vapor deposition or CVD or precursor or SiO2 or "sio. sub.2" or silicon dioxide)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:10
S228	693	S227 and (SiO2 or "sio.sub.2" or silicon dioxide) same (CVD or chemical vapor deposition)	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:10
S229	0	S228 and 427/4.ccls.	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:10
S230	155	S228 and "427"/\$.ccls.	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/15 12:10

S231	1	10/586675 and ethoxysilane	US- PGPUB; USPAT; UPAD	ADJ	ON	2011/07/17 10:11
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7/18/2011 8:22:22 AM

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